

Amendments to the Claims:

Claims 1-18. (Currently canceled)

19. (original) A method of fabricating a transistor source/drain contact between adjacent transistor gate structures comprising:

depositing a filler material at least in a region between the adjacent transistor gate structures;

removing the filler material with a process having a removal selectivity to nitride greater than 40:1 to form a contact opening; and

depositing a conductive material in the contact opening.

20. (original) A method of fabricating a transistor source/drain contact between adjacent transistor gate structures having nitride sidewall spacers comprising:

depositing a filler material at least in a region between the adjacent transistor gate structures;

removing the filler material with a process having a removal selectivity to nitride greater than 40:1 to form a contact opening having an aspect ratio greater than about 5:1; and

depositing a conductive material in the contact opening.

21. (original) A method of fabricating a transistor source/drain connection between adjacent transistor gate structures comprising:

depositing an amorphous carbon filler material at least in a region between the adjacent transistor gate structures;

selectively dry developing the filler material in the region between the adjacent transistor gate structures to form a contact opening; and

depositing a polysilicon material in the contact opening.